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Team Nexperia



PMF77XN

30 V, single N-channel Trench MOSFET Rev. 1 — 27 March 2012

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a SOT323 (SC-70) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching

Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-	1.63	Α
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 1.5 \text{ A}; T_j = 25 \text{ °C}$		-	77	97	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	_	_
2	S	source	3	D
3	D	drain	1 2	G S
			SOT323 (SC-70)	017aaa253



30 V, single N-channel Trench MOSFET

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMF77XN	SC-70	plastic surface-mounted package; 3 leads	SOT323

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMF77XN	V9%

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25 ^{\circ}C$		-	30	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	1.63	Α
		$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	1.5	Α
		$V_{GS} = 4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	1	Α
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \text{ µs}$		-	6	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	270	mW
			<u>[1]</u>	-	350	mW
		T _{sp} = 25 °C		-	1920	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	0.7	Α
·	· · · · · · · · · · · · · · · · · · ·	the control of the co				

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

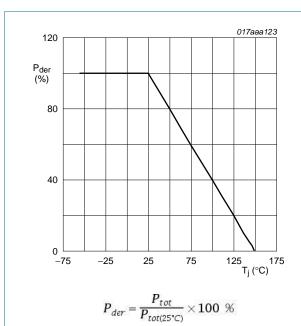


Fig 1. Normalized total power dissipation as a function of junction temperature

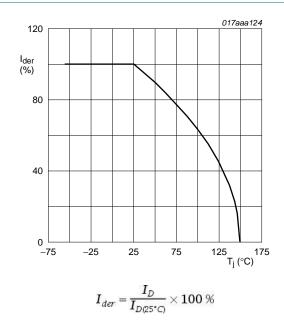
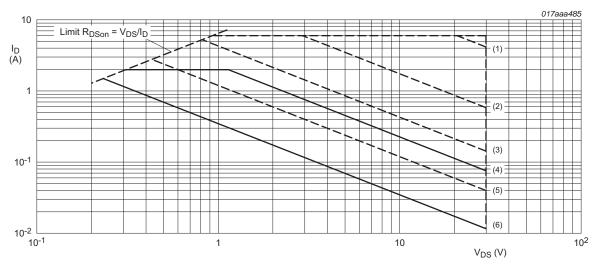


Fig 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

(1)
$$t_p = 100 \, \mu s$$

(2)
$$t_p = 1 \text{ ms}$$

(3)
$$t_p = 10 \text{ ms}$$

(4) DC;
$$T_{sp} = 25$$
 °C

$$(5) t_p = 100 ms$$

(6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 6 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

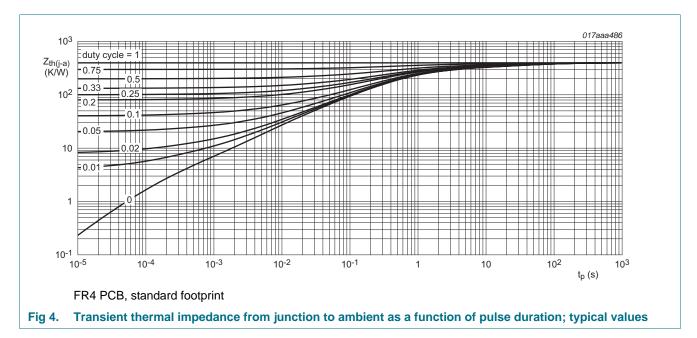
30 V, single N-channel Trench MOSFET

6. Thermal characteristics

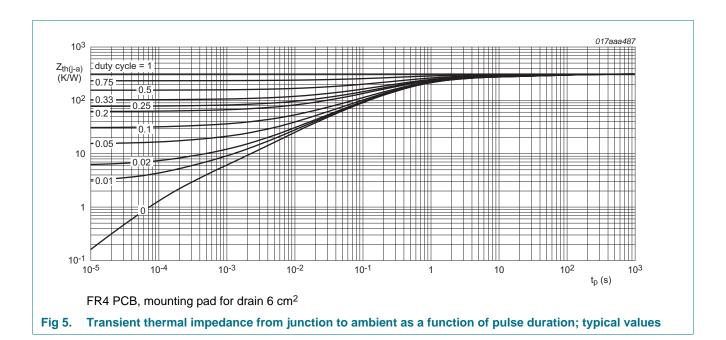
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	402	460	K/W
			[2]	-	312	360	K/W
			[3]	-	265	305	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	55	65	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², t ≤ 5 s.



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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	1	1.5	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 1.5 \text{ A}; T_j = 25 \text{ °C}$	-	77	97	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 1.5 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	122	154	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 0.8 \text{ A}; T_j = 25 \text{ °C}$	-	104	142	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 1.5 \text{ A}; T_j = 25 \text{ °C}$	-	6.5	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 1.5 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	1.9	2.9	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.35	-	nC
Q_{GD}	gate-drain charge		-	0.43	-	nC
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	170	-	pF
Coss	output capacitance	T _j = 25 °C	-	31	-	pF
C _{rss}	reverse transfer capacitance		-	17	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; I_D = 1.5 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	19	-	ns
t _{d(off)}	turn-off delay time		-	27	-	ns
t _f	fall time		-	11	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 0.7 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	0.8	1.2	V

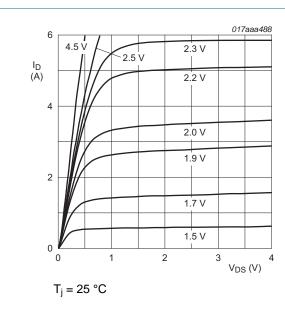


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

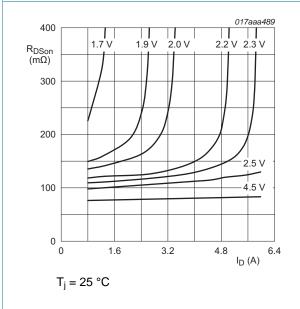
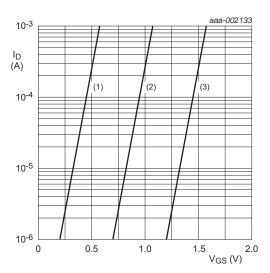


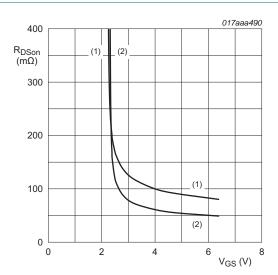
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



$$T_{j} = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

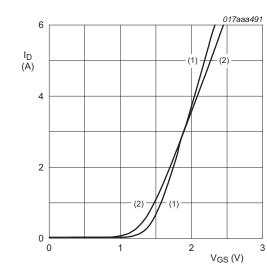


$$I_D = 1.5 A$$

(1)
$$T_i = 150 \, ^{\circ}C$$

(2)
$$T_j = 25 \, {}^{\circ}\text{C}$$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

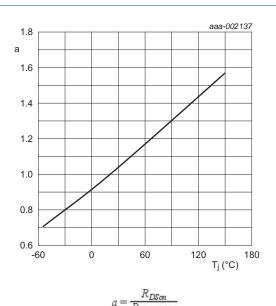
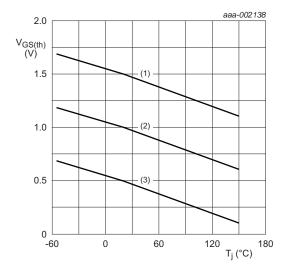


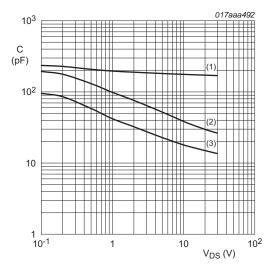
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = 1.5 A; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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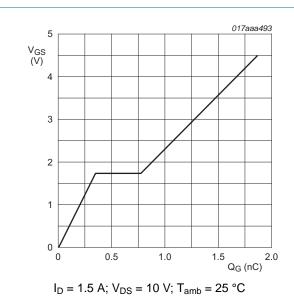


Fig 14. Gate-source voltage as a function of gate charge; typical values

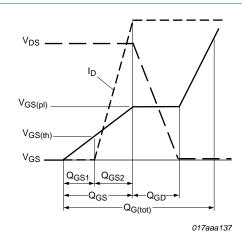
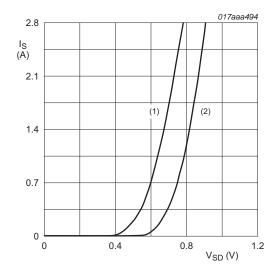


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

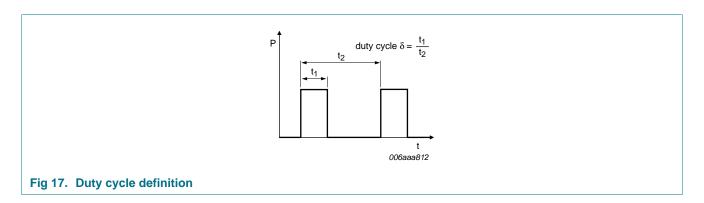
(1) $T_j = 150 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}C$

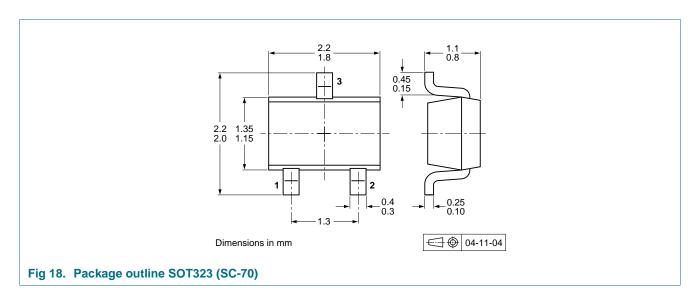
Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information

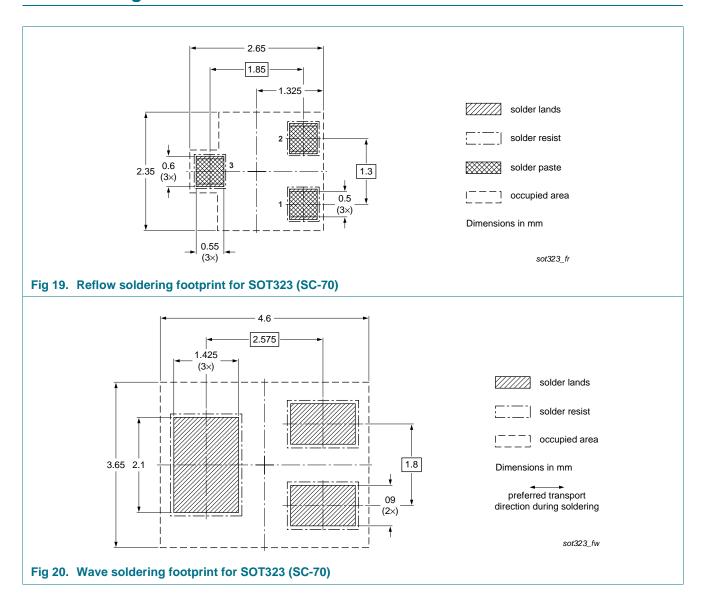


9. Package outline



30 V, single N-channel Trench MOSFET

10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMF77XN v.1	20120327	Product data sheet	-	-

30 V, single N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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